N - Channel 250-V (D-S) MOSFET

GENERAL DESCRIPTION

The ME2326A is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance.

FEATURES

- $R_{DS(ON)} \leqq 5.5\Omega @ V_{GS}=10V$
- $R_{DS(ON)} \leqq 5.5\Omega @ V_{GS}=4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability

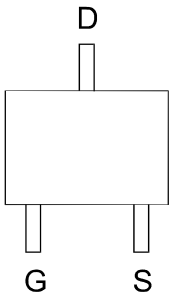
APPLICATIONS

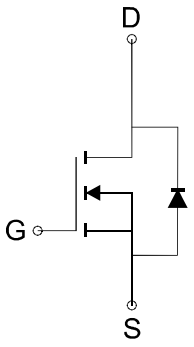
- Power Management in Note book
- DC/DC Converter
- Load Switch
- LCD Display inverter

PIN CONFIGURATION

(SOT-23)

Top View





N-Channel MOSFET

Ordering Information: ME2326A(Pb-free)

ME2326A-G (Green product-Halogen free)

Absolute Maximum Ratings (T_A=25℃ Unless Otherwise Noted)

Parameter		Symbol	Maximum Ratings	Unit
Drain-Source Voltage		V_{DS}	250	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25℃	I_D	0.4	A
	T_A=70℃		0.3	
Pulsed Drain Current		I_{DM}	1.6	A
Maximum Power Dissipation	T_A=25℃	P_D	1.4	W
	T_A=70℃		0.9	
Operating Junction Temperature		T_J	150	℃
Storage Temperature Range		T_{stg}	-55 to 150	℃
Thermal Resistance-Junction to Ambient*		$R_{\theta JA}$	90	℃/W

* The device mounted on 1in^2 FR4 board with 2 oz copper

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Electrical Characteristics (T_A=25℃ Unless Otherwise Specified)

Symbol	Parameter	Limit	Min	Typ	Max	Unit
STATIC						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	250			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1.0		3.0	V
I_{GSS}	Gate-Body Leakage	V_{DS}=0V, V_{GS}=±20V			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=250V, V_{GS}=0V			1	μA
$R_{DS(ON)}$	Drain-Source On-Resistance*	V_{GS}=10V, I_D=250mA		4.5	5.5	Ω
		V_{GS}=4.5V, I_D=250mA		4.5	5.5	
V_{SD}	Diode Forward Voltage *	I_S=250mA, V_{GS}=0V		0.8	1.2	V
DYNAMIC						
Qg	Total Gate Charge	V_{DS}=10V, V_{GS}=10V, I_D=1.2A		11.2		nC
Qg	Total Gate Charge	V_{DS}=10V, V_{GS}=4.5V, I_D=1.2A		4.1		
Qgs	Gate-Source Charge			2.6		
Qgd	Gate-Drain Charge			0.9		
Ciss	Input Capacitance	V_{DS}=15V, V_{GS}=0V, f=1MHz		361		pF
Coss	Output Capacitance			16		
Crss	Reverse Transfer Capacitance			5.6		
$t_{d(on)}$	Turn-On Delay Time	V_{DD}=25V, R_L=25Ω, R_G=25Ω, V_{GEN}=10V,		9.7		ns
tr	Turn-On Rise Time			25.6		
$t_{d(off)}$	Turn-Off Delay Time			236		
t_f	Turn-Off Fall Time			275		

Notes: a. pulse test: pulse width≦ 300us, duty cycle≦ 2%, Guaranteed by design, not subject to production testing.

b. Matsuki Electric/ Force mos reserves the right to improve product design, functions and reliability without notice.

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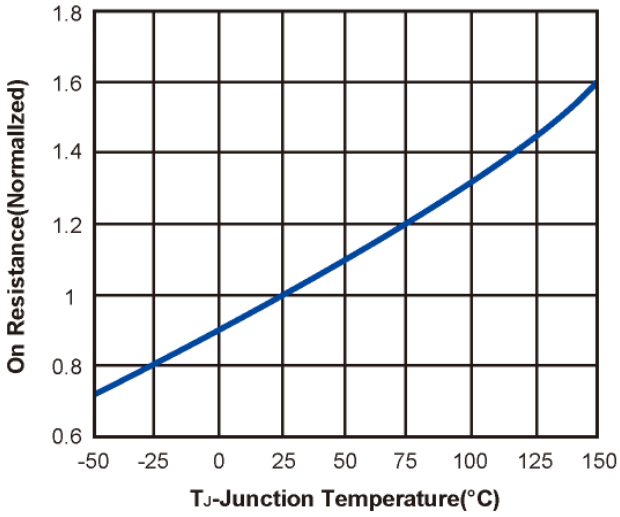
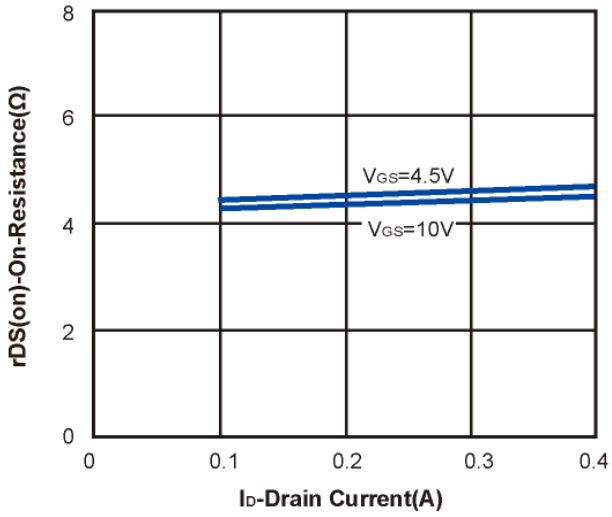
Typical Characteristics (T_J =25℃ Noted)

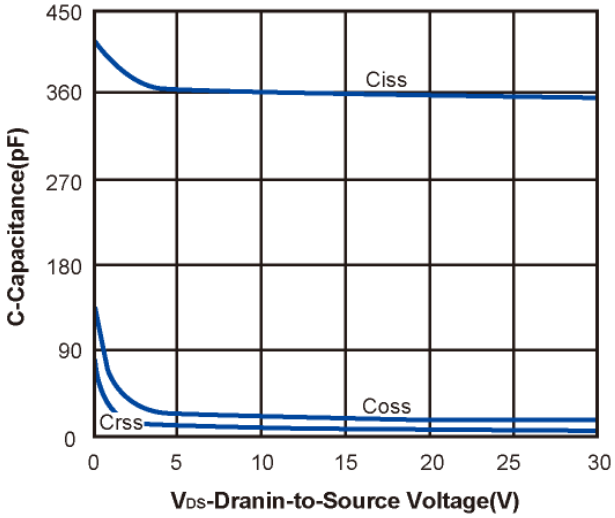
On Resistance vs. Junction Temperature



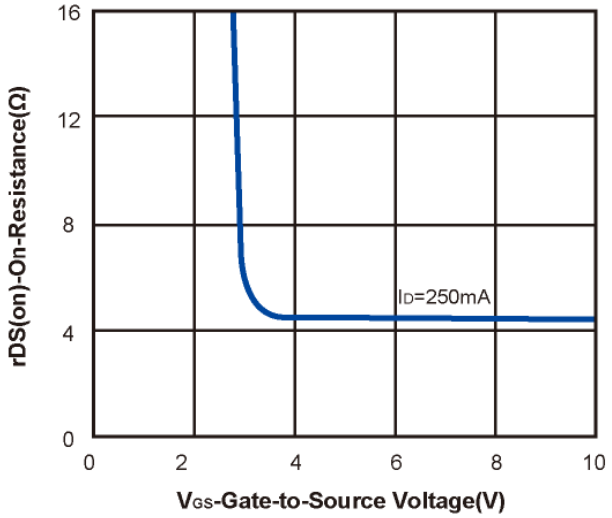
On Resistance vs. Drain Current



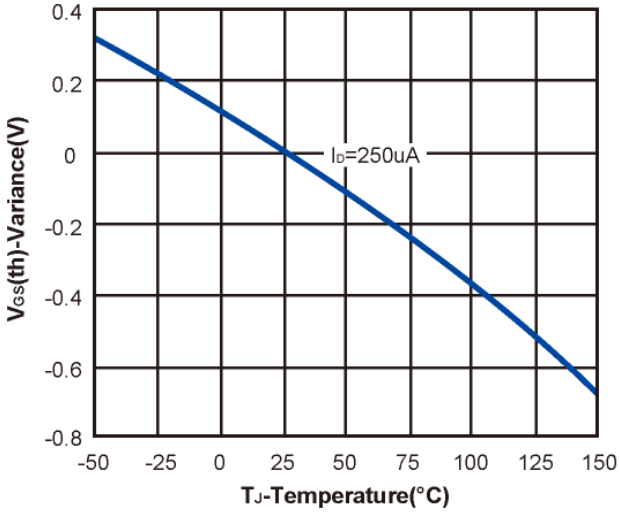
Capacitance



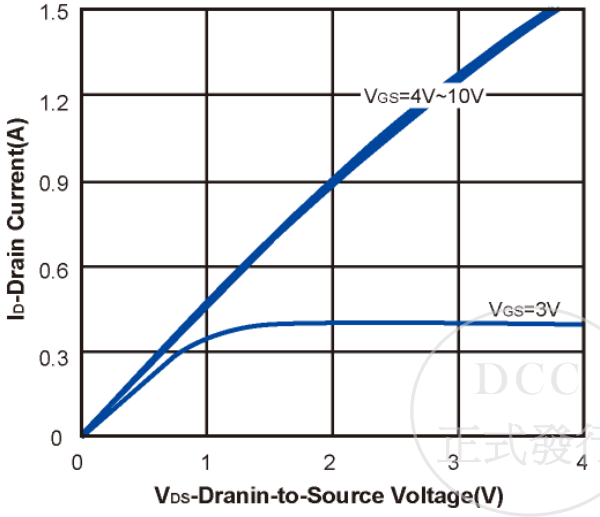
On Resistance vs. Gate-to-Source Voltage



Threshold Voltage



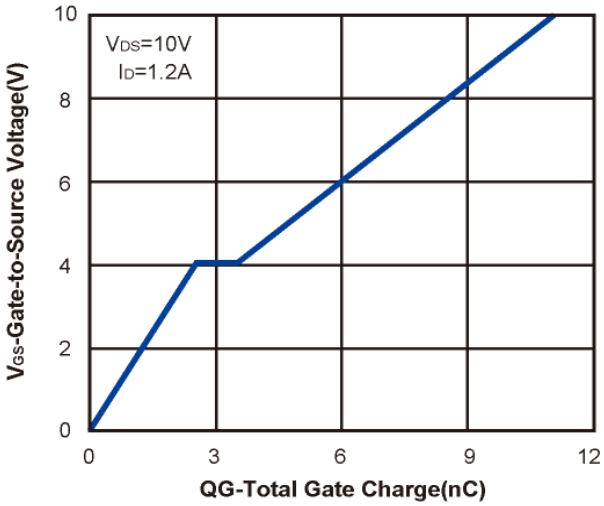
On-Region Characteristics



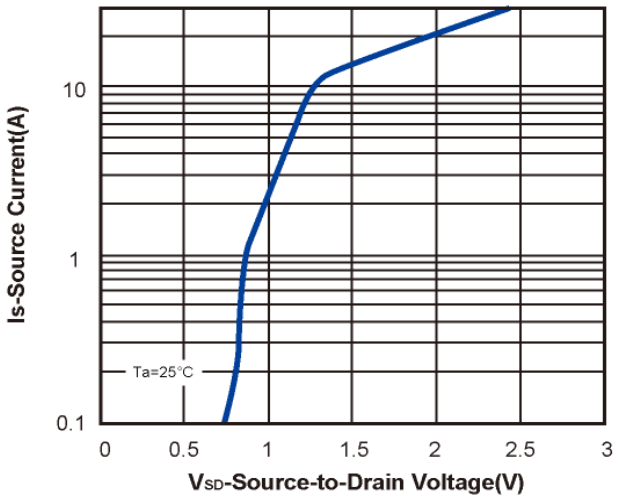
N - Channel 250-V (D-S) MOSFET

Typical Characteristics (T_J =25℃ Noted)

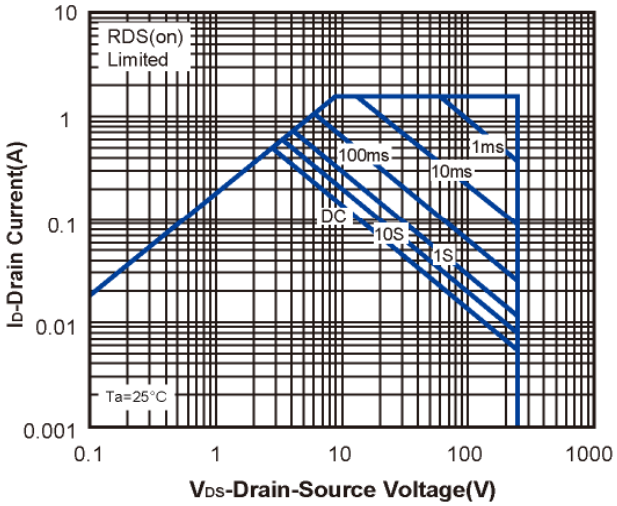
Gate Charge



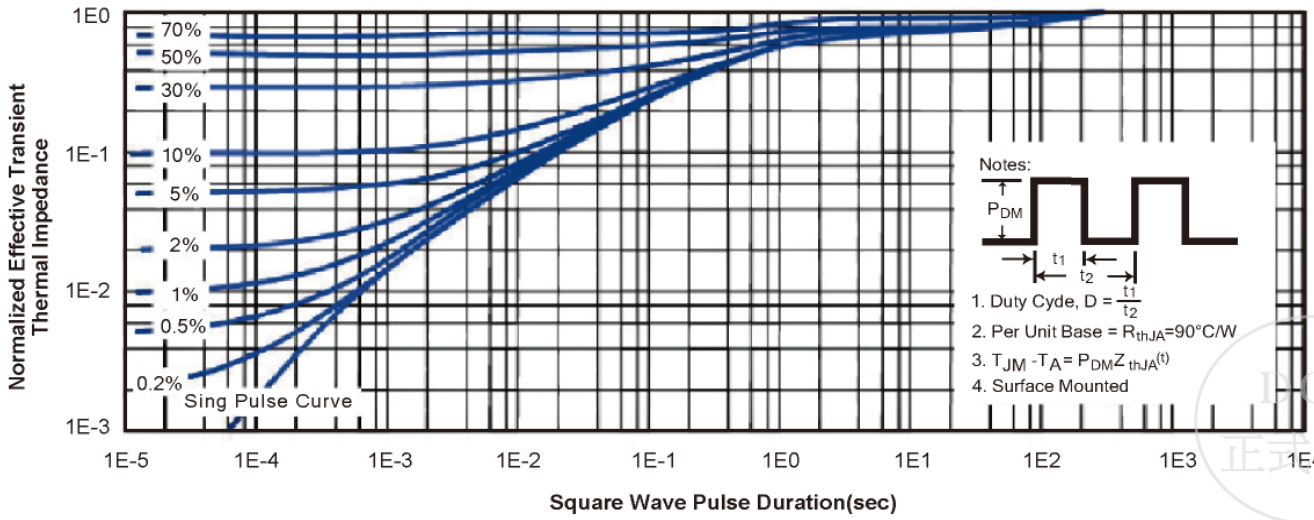
Body-diode characteristics



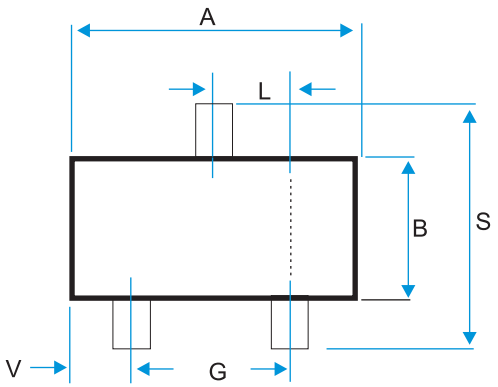
Maximum Forward Biased Safe Operating Area

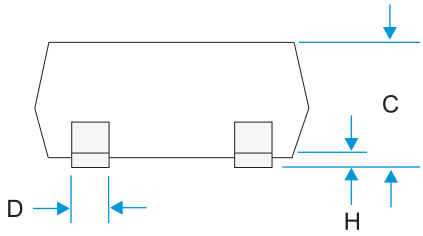


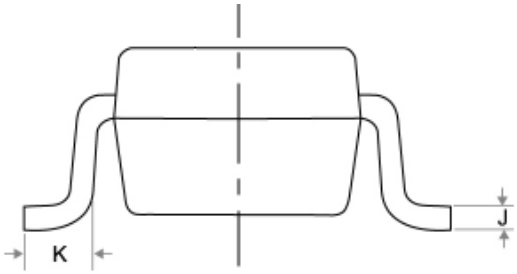
Normalized Thermal Transient Impedance, Junction-to-Ambient



SOT-23 Package Outline







Symbol	MILLIMETERS (mm)	
	MIN	MAX
A	2.800	3.00
B	1.200	1.70
C	0.900	1.30
D	0.350	0.50
G	1.780	2.04
H	0.010	0.15
J	0.085	0.20
K	0.300	0.65
L	0.890	1.02
S	2.100	3.00
V	0.450	0.60